

LP2998/LP2998-Q1 DDR Termination Regulator

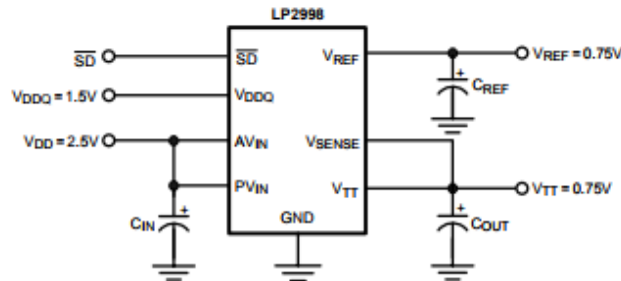
1 Features

- AEC-Q100 Test Guidance with the following results (SO PowerPAD-8):
 - Device HBM ESD Classification Level H1C
 - Junction Temperature Range -40°C to 125°C
- 1.35 V Minimum V_{DDQ}
- Source and Sink Current
- Low Output Voltage Offset
- No External Resistors Required
- Linear Topology
- Suspend to Ram (STR) Functionality
- Low External Component Count
- Thermal Shutdown

2 Applications

- DDR1, DDR2, DDR3, and DDR3L Termination Voltage
- Automotive Infotainment
- FPGA
- Industrial/Medical PC
- SSTL-18, SSTL-2, and SSTL-3 Termination
- HSTL Termination

4 Simplified Schematic



3 Description

The LP2998 linear regulator is designed to meet JEDEC SSTL-2 and JEDEC SSTL-18 specifications for termination of DDR-SDRAM and DDR2 memory. The device also supports DDR3 and DDR3L VTT bus termination with V_{DDQ} min of 1.35 V. The device contains a high-speed operational amplifier to provide excellent response to load transients. The output stage prevents shoot through while delivering 1.5 A continuous current and transient peaks up to 3 A in the application as required for DDR-SDRAM termination. The LP2998 also incorporates a VSENSE pin to provide superior load regulation and a V_{REF} output as a reference for the chipset and DIMMs.

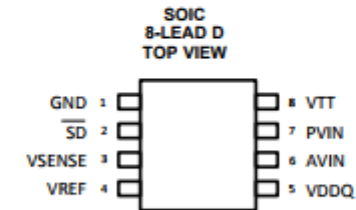
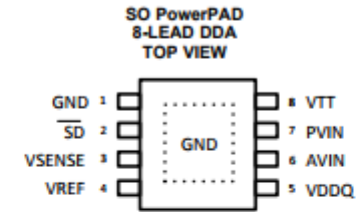
An additional feature found on the LP2998 is an active low shutdown ($\overline{\text{SD}}$) pin that provides Suspend To RAM (STR) functionality. When $\overline{\text{SD}}$ is pulled low the V_{TT} output will tri-state providing a high impedance output, but, V_{REF} will remain active. A power savings advantage can be obtained in this mode through lower quiescent current.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
LP2998	SO PowerPAD™ (8)	4.89 mm x 3.90 mm
LP2998	SOIC (8)	4.90 mm x 3.91 mm
LP2998-Q1	SO PowerPAD™ (8)	4.89 mm x 3.90 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.

6 Pin Configuration and Functions



Pin Functions

PIN		
NUMBER	TYPE	DESCRIPTION
1	GND	Ground
2	$\overline{\text{SD}}$	Shutdown
3	VSENSE	Feedback pin for regulating V_{TT} .
4	VREF	Buffered internal reference voltage of $V_{\text{DDQ}}/2$
5	VDDQ	Input for internal reference equal to $V_{\text{DDQ}}/2$
6	AVIN	Analog input pin
7	PVIN	Power input pin
8	VTT	Output voltage for connection to termination resistors
	EP	Exposed pad thermal connection. Connect to Ground.

6.1 Pin Descriptions

AVIN AND PVIN	AVIN and PVIN are the input supply pins for the LP2998. AVIN is used to supply all the internal control circuitry. PVIN, however, is used exclusively to provide the rail voltage for the output stage used to create VTT. These pins have the capability to work off separate supplies depending on the application. Higher voltages on PVIN will increase the maximum continuous output current because of output R _{DS(on)} limitations at voltages close to VTT. The disadvantage of high values of PVIN is that the internal power loss will also increase, thermally limiting the design. For SSTL-2 applications, a good compromise would be to connect the AVIN and PVIN directly together at 2.5 V. This eliminates the need for bypassing the two supply pins separately. The only limitation on input voltage selection is that PVIN must be equal to or lower than AVIN. It is recommended to connect PVIN to voltage rails equal to or less than 3.3 V to prevent the thermal limit from tripping because of excessive internal power dissipation. If the junction temperature exceeds the thermal shutdown then the part will enter a shutdown state identical to the manual shutdown where VTT is tri-stated and VREF remains active.
VDDQ	VDDQ is the input used to create the internal reference voltage for regulating VTT. The reference voltage is generated from a resistor divider of two internal 50 kΩ resistors. This ensures that VTT will track VDDQ / 2 precisely. The optimal implementation of VDDQ is as a remote sense. This can be achieved by connecting VDDQ directly to the 2.5 V rail at the DIMM instead of AVIN and PVIN. This ensures that the reference voltage tracks the DDR memory rails precisely without a large voltage drop from the power lines. For SSTL-2 applications VDDQ will be a 2.5 V signal, which will create a 1.25 V termination voltage at VTT (See Electrical Characteristics Table for exact values of VTT over temperature).

Pin Descriptions (continued)

V_{SENSE}	The purpose of the sense pin is to provide improved remote load regulation. In most motherboard applications the termination resistors will connect to V _{TT} in a long plane. If the output voltage was regulated only at the output of the LP2998 then the long trace will cause a significant IR drop resulting in a termination voltage lower at one end of the bus than the other. The V _{SENSE} pin can be used to improve this performance, by connecting it to the middle of the bus. This will provide a better distribution across the entire termination bus. If remote load regulation is not used then the V _{SENSE} pin must still be connected to V _{TT} . Care should be taken when a long V _{SENSE} trace is implemented in close proximity to the memory. Noise pickup in the V _{SENSE} trace can cause problems with precise regulation of V _{TT} . A small 0.1 μ F ceramic capacitor placed next to the V _{SENSE} pin can help filter any high frequency signals and preventing errors.
SHUTDOWN	The LP2998 contains an active low shutdown pin that can be used to tri-state V _{TT} . During shutdown V _{TT} should not be exposed to voltages that exceed AVIN. With the shutdown pin asserted low the quiescent current of the LP2998 will drop, however, V _{DDQ} will always maintain its constant impedance of 100 k Ω for generating the internal reference. Therefore, to calculate the total power loss in shutdown both currents need to be considered. For more information refer to the <i>Thermal Dissipation</i> section. The shutdown pin also has an internal pull-up current, therefore to turn the part on the shutdown pin can either be connected to AVIN or left open.
V_{REF}	V _{REF} provides the buffered output of the internal reference voltage V _{DDQ} / 2. This output should be used to provide the reference voltage for the Northbridge chipset and memory. Since these inputs are typically an extremely high impedance, there should be little current drawn from V _{REF} . For improved performance, an output bypass capacitor can be used, located close to the pin, to help with noise. A ceramic capacitor in the range of 0.1 μ F to 0.01 μ F is recommended. This output remains active during the shutdown state and thermal shutdown events for the suspend to RAM functionality.
V_{TT}	V _{TT} is the regulated output that is used to terminate the bus resistors. It is capable of sinking and sourcing current while regulating the output precisely to V _{DDQ} / 2. The LP2998 is designed to handle peak transient currents of up to ± 3 A with a fast transient response. The maximum continuous current is a function of V _{IN} and can be viewed in the <i>Typical Characteristics</i> section. If a transient is expected to last above the maximum continuous current rating for a significant amount of time then the output capacitor should be sized large enough to prevent an excessive voltage drop. Despite the fact that the LP2998 is designed to handle large transient output currents it is not capable of handling these for long durations, under all conditions. The reason for this is the standard packages are not able to thermally dissipate the heat as a result of the internal power loss. If large currents are required for longer durations, then care should be taken to ensure that the maximum junction temperature is not exceeded. Proper thermal derating should always be used (please refer to the <i>Thermal Dissipation</i> section). If the junction temperature exceeds the thermal shutdown point than V _{TT} will tri-state until the part returns below the hysteretic trip-point.

7 Specifications

7.1 Absolute Maximum Ratings ⁽¹⁾⁽²⁾

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
AVIN to GND	-0.3	6	V
PVIN to GND	-0.3	AVIN	V
V _{DDQ} ⁽³⁾	-0.3	6	V
Junction temperature		150	$^{\circ}$ C
Lead temperature (soldering, 10 sec)		260	$^{\circ}$ C

- (1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/Distributors for availability and specifications.
- (3) V_{DDQ} voltage must be less than 2 x (AVIN - 1) or 6V, whichever is smaller.

7.2 Handling Ratings: LP2998

	MIN	MAX	UNIT
T _{stg}	Storage temperature range		-65 150 $^{\circ}$ C
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANS/ESDA/JEDEC JS-001, all pins ⁽¹⁾	-1000 1000 V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

7.3 Handling Ratings: LP2998-Q1

	MIN	MAX	UNIT
T _{stg}	Storage temperature range		-65 150 $^{\circ}$ C
V _(ESD)	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾	-1000 1000 V

- (1) AEC Q100-002 indicates HBM stressing is done in accordance with the ANS/ESDA/JEDEC JS-001 specification. The LP2998-Q1 is rated at AEC-Q100 ESD HBM Classification Level H1C.

7.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	NOM	MAX	UNIT
Junction temperature ⁽¹⁾	-40		125	$^{\circ}$ C
AVIN to GND	2.2		5.5	V
PVIN supply voltage	0		AVIN	V
SD input voltage	0		AVIN	V

- (1) At elevated temperatures, devices must be derated based on thermal resistance.

7.5 Thermal Information

THERMAL METRIC ⁽¹⁾	LP2998/LP2998-Q1	LP2998	UNIT
	SO PowerPAD	SOIC	
	8 PINS	8 PINS	
R _{thJA} Junction-to-ambient thermal resistance	43	151	$^{\circ}$ C/W

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

7.6 Electrical Characteristics

Typical limits tested at $T_J = 25^\circ\text{C}$. Minimum and maximum limits apply over the full operating junction temperature range ($T_J = -40^\circ\text{C}$ to 125°C).⁽¹⁾ Unless otherwise specified, $AVIN = PVIN = 2.5\text{ V}$, $VDDQ = 2.5\text{ V}$.⁽²⁾

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{REF}	V _{REF} voltage (DDR I)	VIN = VDDQ = 2.3 V	1.135	1.158	1.185	V
		VIN = VDDQ = 2.5 V	1.235	1.258	1.285	
		VIN = VDDQ = 2.7 V	1.335	1.358	1.385	
	V _{REF} voltage (DDR II)	PVIN = VDDQ = 1.7 V	0.837	0.860	0.887	
		PVIN = VDDQ = 1.8 V	0.887	0.910	0.937	
		PVIN = VDDQ = 1.9 V	0.936	0.959	0.986	
	V _{REF} Voltage (DDR III)	PVIN = VDDQ = 1.35V	0.669	0.684	0.699	
		PVIN = VDDQ = 1.5V	0.743	0.758	0.773	
		PVIN = VDDQ = 1.6V	0.793	0.808	0.823	
Z _{VREF}	V _{REF} Output Impedance	I _{REF} = -30 to 30 μA	2.5		k Ω	
V _{TT}	V _{TT} Output Voltage (DDR I) ⁽³⁾	I _{OUT} = 0 A				V
		VIN = VDDQ = 2.3 V	1.120	1.159	1.190	
		VIN = VDDQ = 2.5 V	1.210	1.259	1.290	
		VIN = VDDQ = 2.7 V	1.320	1.359	1.390	
		I _{OUT} = $\pm 1.5\text{ A}$				
		VIN = VDDQ = 2.3 V	1.125	1.159	1.190	
		VIN = VDDQ = 2.5 V	1.225	1.259	1.290	
V _{TT} Output Voltage (DDR II) ⁽³⁾	I _{OUT} = 0 A, AVIN = 2.5 V				V	
	PVIN = VDDQ = 1.7 V	0.822	0.856	0.887		
	PVIN = VDDQ = 1.8 V	0.874	0.908	0.939		
	PVIN = VDDQ = 1.9 V	0.923	0.957	0.988		
	I _{OUT} = $\pm 0.5\text{ A}$, AVIN = 2.5 V					
	PVIN = VDDQ = 1.7 V	0.820	0.856	0.890		
	PVIN = VDDQ = 1.8 V	0.870	0.908	0.940		
PVIN = VDDQ = 1.9 V	0.920	0.957	0.990			
V _{TT} Output Voltage (DDR III) ⁽³⁾	I _{OUT} = 0A, AVIN = 2.5 V				V	
	PVIN = VDDQ = 1.35V	0.656	0.677	0.698		
	PVIN = VDDQ = 1.5 V	0.731	0.752	0.773		
	PVIN = VDDQ = 1.6 V	0.781	0.802	0.823		
	I _{OUT} = 0.2 A, AVIN = 2.5V PVIN = VDDQ = 1.35V	0.667	0.688	0.710		
	I _{OUT} = -0.2A, AVIN = 2.5V PVIN = VDDQ = 1.35V	0.641	0.673	0.694		
	I _{OUT} = 0.4 A, AVIN = 2.5 V PVIN = VDDQ = 1.5 V	0.740	0.763	0.786		
	I _{OUT} = -0.4 A, AVIN = 2.5 V PVIN = VDDQ = 1.5 V	0.731	0.752	0.773		
	I _{OUT} = 0.5 A, AVIN = 2.5 V PVIN = VDDQ = 1.6 V	0.790	0.813	0.836		
I _{OUT} = -0.5 A, AVIN = 2.5 V PVIN = VDDQ = 1.6 V	0.781	0.802	0.823			

Electrical Characteristics (continued)

Typical limits tested at $T_J = 25^\circ\text{C}$. Minimum and maximum limits apply over the full operating junction temperature range ($T_J = -40^\circ\text{C}$ to 125°C).⁽¹⁾ Unless otherwise specified, $AVIN = PVIN = 2.5\text{ V}$, $VDDQ = 2.5\text{ V}$.⁽²⁾

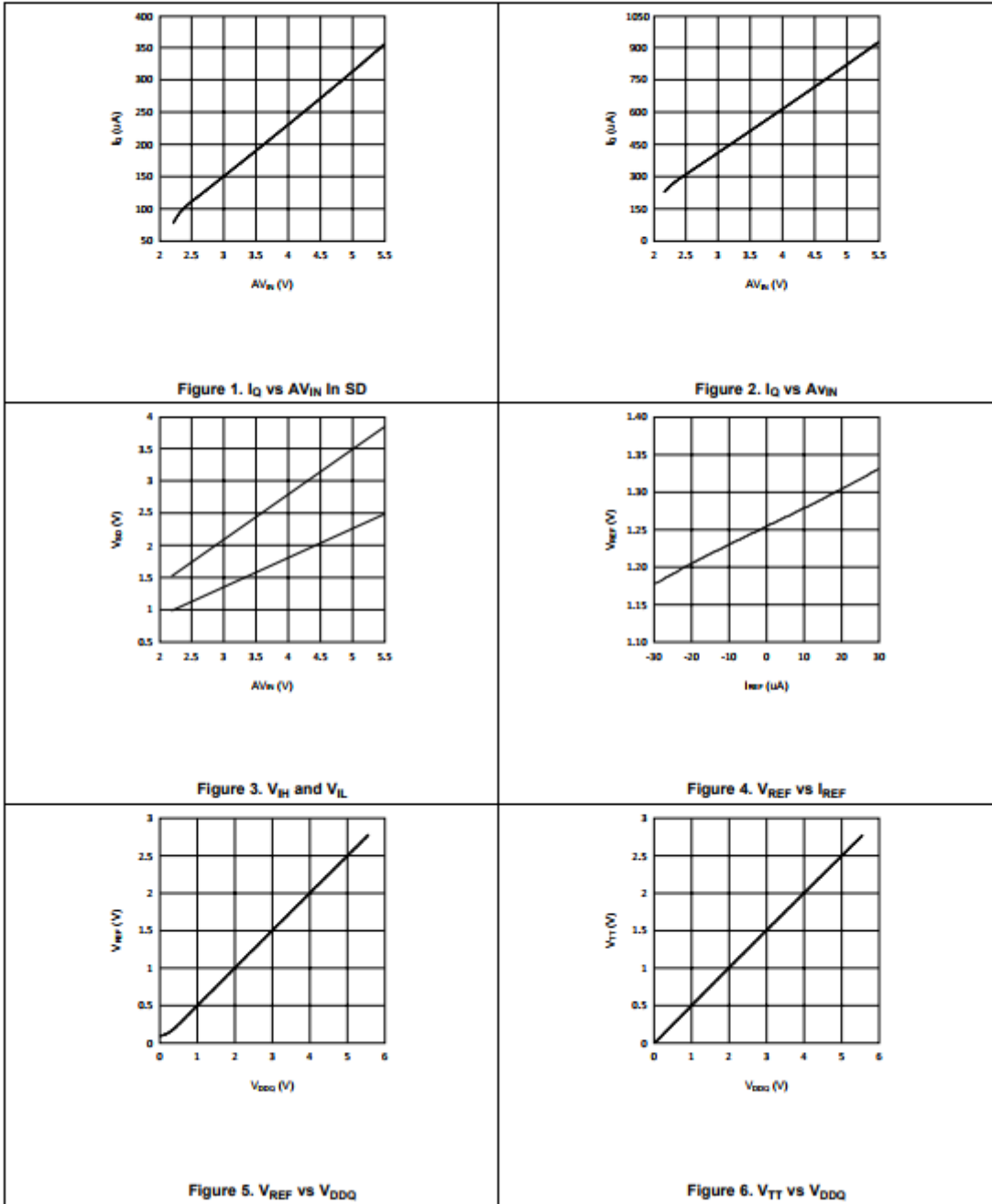
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{OS_VTT}	V _{TT} Output Voltage Offset ($V_{REF} - V_{TT}$) for DDR I ⁽³⁾	I _{OUT} = 0 A	-30	0	30	mV
		I _{OUT} = -1.5 A	-30	0	30	
		I _{OUT} = 1.5 A	-30	0	30	
	V _{TT} Output Voltage Offset ($V_{REF} - V_{TT}$) for DDR II ⁽³⁾	I _{OUT} = 0 A	-30	0	30	
		I _{OUT} = -0.5 A	-30	0	30	
		I _{OUT} = 0.5 A	-30	0	30	
	V _{TT} Output Voltage Offset ($V_{REF} - V_{TT}$) for DDR III ⁽³⁾	I _{OUT} = 0 A	-30	0	30	
		I _{OUT} = $\pm 0.2\text{ A}$	-30	0	30	
		I _{OUT} = $\pm 0.4\text{ A}$	-30	0	30	
I _{OUT} = $\pm 0.5\text{ A}$	-30	0	30			
I _Q	Quiescent Current ⁽⁴⁾	I _{OUT} = 0 A		320	500	μA
Z _{VDDQ}	VDDQ Input Impedance		100			k Ω
I _{SD}	Quiescent current in shutdown ⁽⁴⁾	SD = 0 V		115	150	μA
I _{Q_SD}	Shutdown leakage current	SD = 0 V		2	5	μA
V _H	Minimum Shutdown High Level		1.9			V
V _{IL}	Maximum Shutdown Low Level				0.8	V
I _V	V _{TT} leakage current in shutdown	SD = 0 V V _{TT} = 1.25 V		1	10	μA
I _{SENSE}	V _{SENSE} Input current			13		nA
T _{SD}	Thermal Shutdown ⁽⁵⁾			165		$^\circ\text{C}$
T _{SD_HYS}	Thermal Shutdown Hysteresis			10		$^\circ\text{C}$

(4) Quiescent current defined as the current flow into AVIN.

(5) The maximum allowable power dissipation is a function of the maximum junction temperature, $T_{J(\text{MAX})}$, the junction to ambient thermal resistance, $R_{\theta JA}$, and the ambient temperature, T_A . Exceeding the maximum allowable power dissipation will cause excessive die temperature and the regulator will go into thermal shutdown.

7.7 Typical Characteristics

Unless otherwise specified AVIN = PVIN = 2.5 V.

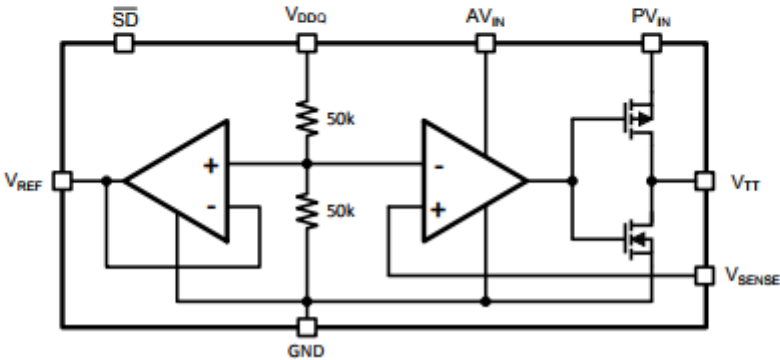


8 Detailed Description

8.1 Overview

The LP2998 linear regulator is designed to meet JEDEC SSTL-2 and JEDEC SSTL-18 specifications for termination of DDR-SDRAM and DDR2 memory. The device also supports DDR3 and DDR3L VTT bus termination with V_{DDQ} min of 1.35 V. The device contains a high-speed operational amplifier to provide excellent response to load transients. The output stage prevents shoot through while delivering 1.5 A continuous current and transient peaks up to 3 A in the application as required for DDR-SDRAM termination.

8.2 Functional Block Diagram



8.3 Feature Description

The LP2998 is a linear bus termination regulator designed to meet the JEDEC requirements of SSTL-2 and SSTL-18. The output, V_{TT} is capable of sinking and sourcing current while regulating the output voltage equal to $V_{DDQ} / 2$. The output stage has been designed to maintain excellent load regulation while preventing shoot through. The LP2998 also incorporates two distinct power rails that separates the analog circuitry from the power output stage. This allows a split rail approach to be utilized to decrease internal power dissipation. It also permits the LP2998 to provide a termination solution for DDR3-SDRAM and DDR3L-SDRAM memory.

8.4 Device Functional Modes

The LP2998 can also be used to provide a termination voltage for other logic schemes such as SSTL-3 or HSTL. Series Stub Termination Logic (SSTL) was created to improve signal integrity of the data transmission across the memory bus. This termination scheme is essential to prevent data error from signal reflections while transmitting at high frequencies encountered with DDR-SDRAM. The most common form of termination is Class II single parallel termination. This involves one R_S series resistor from the chipset to the memory and one R_T termination resistor. Typical values for R_S and R_T are 25 Ω , although these can be changed to scale the current requirements from the LP2998. This implementation can be seen below in Figure 16.

9 Application and Implementation

9.1 Application Information

9.1.1 Input Capacitor

The LP2998 does not require a capacitor for input stability, but it is recommended for improved performance during large load transients to prevent the input rail from dropping. The input capacitor should be located as close as possible to the PVIN pin. Several recommendations exist dependent on the application required. A typical value recommended for AL electrolytic capacitors is 50 μF . Ceramic capacitors can also be used, a value in the range of 10 μF with X5R or better would be an ideal choice. The input capacitance can be reduced if the LP2998 is placed close to the bulk capacitance from the output of the 2.5 V DC-DC converter. If the two supply rails (AVIN and PVIN) are separated then the 47 μF capacitor should be placed as close to possible to the PVIN rail. An additional 0.1 μF ceramic capacitor can be placed on the AVIN rail to prevent excessive noise from coupling into the device.

9.1.2 Output Capacitor

The LP2998 has been designed to be insensitive of output capacitor size or ESR (Equivalent Series Resistance). This allows the flexibility to use any capacitor desired. The choice for output capacitor will be determined solely on the application and the requirements for load transient response of V_{TT} . As a general recommendation the output capacitor should be sized above 100 μF with a low ESR for SSTL applications with DDR-SDRAM. The value of ESR should be determined by the maximum current spikes expected and the extent at which the output voltage is allowed to droop. Several capacitor options are available on the market and a few of these are highlighted below:

AL - It should be noted that many aluminum electrolytics only specify impedance at a frequency of 120 Hz, which indicates they have poor high frequency performance. Only aluminum electrolytics that have an impedance specified at a higher frequency (between 20 kHz and 100 kHz) should be used for the LP2998. To improve the ESR several AL electrolytics can be combined in parallel for an overall reduction. An important note to be aware of is the extent at which the ESR will change over temperature. Aluminum electrolytic capacitors can have their ESR rapidly increase at cold temperatures.

Ceramic - Ceramic capacitors typically have a low capacitance, in the range of 10 to 100 μF range, but they have excellent AC performance for bypassing noise because of very low ESR (typically less than 10 m Ω). However, some dielectric types do not have good capacitance characteristics as a function of voltage and temperature. Because of the typically low value of capacitance it is recommended to use ceramic capacitors in parallel with another capacitor such as an aluminum electrolytic. A dielectric of X5R or better is recommended for all ceramic capacitors.

Hybrid - Several hybrid capacitors such as OS-CON and SP are available from several manufacturers. These offer a large capacitance while maintaining a low ESR. These are the best solution when size and performance are critical, although their cost is typically higher than any other capacitor.

9.1.3 Thermal Dissipation

Since the LP2998 is a linear regulator any current flow from V_{TT} will result in internal power dissipation generating heat. To prevent damaging the part from exceeding the maximum allowable junction temperature, care should be taken to derate the part dependent on the maximum expected ambient temperature and power dissipation. The maximum allowable internal temperature rise (T_{Rmax}) can be calculated given the maximum ambient temperature (T_{Amax}) of the application and the maximum allowable junction temperature (T_{Jmax}).

$$T_{\text{Rmax}} = T_{\text{Jmax}} - T_{\text{Amax}}$$

From this equation, the maximum power dissipation (P_{Dmax}) of the part can be calculated:

$$P_{\text{Dmax}} = T_{\text{Rmax}} / R_{\theta\text{JA}}$$

The $R_{\theta\text{JA}}$ of the LP2998 will be dependent on several variables: the package used; the thickness of copper; the number of vias and the airflow.

Application Information (continued)

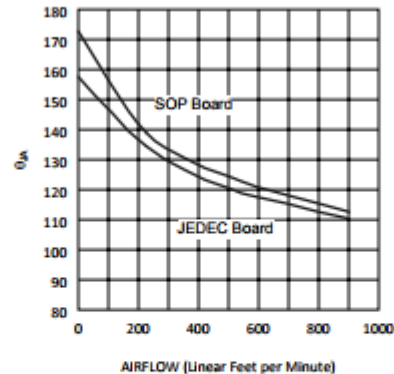


Figure 17. $R_{\theta\text{JA}}$ vs Airflow (SOIC-8)

Additional improvements can be made by the judicious use of vias to connect the part and dissipate heat to an internal ground plane. Using larger traces and more copper on the top side of the board can also help. With careful layout it is possible to reduce the $R_{\theta\text{JA}}$ further than the nominal values shown in Figure 17.

Layout is also extremely critical to maximize the output current with the SO PowerPAD package. By simply placing vias under the DAP the θ_{JA} can be lowered significantly.

Additional improvements in lowering the $R_{\theta\text{JA}}$ can also be achieved with a constant airflow across the package. Maintaining the same conditions as above and utilizing the 2x2 via array, Figure 18 shows how the $R_{\theta\text{JA}}$ varies with airflow.

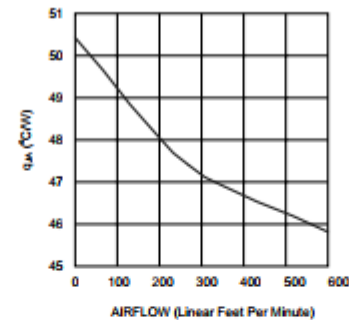


Figure 18. $R_{\theta\text{JA}}$ vs Airflow Speed (Jedec Board with 4 Vias)

- (1) Optimizing the $R_{\theta\text{JA}}$ and placing the LP2998 in a section of a board exposed to lower ambient temperature allows the part to operate with higher power dissipation. The internal power dissipation can be calculated by summing the three main sources of loss: output current at V_{TT} , either sinking or sourcing, and quiescent current at AVIN and VDDQ. During the active state (when shutdown is not held low) the total internal power dissipation can be calculated from the following equations:

$$P_{\text{D}} = P_{\text{AVIN}} + P_{\text{VDDQ}} + P_{\text{VTT}} \tag{3}$$

$$P_{\text{AVIN}} = I_{\text{AVIN}} * V_{\text{AVIN}} \tag{4}$$

$$P_{\text{VDDQ}} = V_{\text{VDDQ}} * I_{\text{VDDQ}} = V_{\text{VDDQ2}} * R_{\text{VDDQ}} \tag{5}$$

To calculate the maximum power dissipation at V_{TT} both conditions at V_{TT} need to be examined, sinking, and sourcing current. Although only one equation will add into the total, V_{TT} cannot source and sink current simultaneously.

Application Information (continued)

$$P_{V_{TT}} = V_{V_{TT}} \times I_{LOAD} \text{ (Sinking) or}$$

$$P_{V_{TT}} = (V_{P_{VIN}} - V_{V_{TT}}) \times I_{LOAD} \text{ (Sourcing)}$$

The power dissipation of the LP2998 can also be calculated during the shutdown state. During this condition the output V_{TT} will tri-state, therefore that term in the power equation will disappear as it cannot sink or source any current (leakage is negligible). The only losses during shutdown will be the reduced quiescent current at AVIN and the constant impedance that is seen at the VDDQ pin.

$$P_D = P_{AVIN} + P_{VDDQ}$$

$$P_{AVIN} = I_{AVIN} \times V_{AVIN}$$

$$P_{VDDQ} = V_{VDDQ} \times I_{VDDQ} = V_{VDDQ2} \times R_{VDDQ}$$

9.2 Typical Application

Several different application circuits are shown below to illustrate some of the options that are possible in configuring the LP2998. Graphs of the individual circuit performance can be found in the *Typical Characteristics* section. These curves illustrate how the maximum output current is affected by changes in AVIN and PVIN.

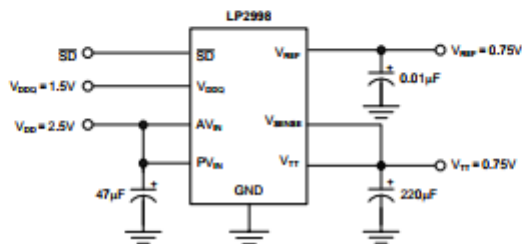


Figure 19. Typical Application Circuit

9.2.1 DDR-III Applications

With the separate VDDQ pin and an internal resistor divider it is possible to use the LP2998 in applications utilizing DDR-III memory. The output stage is connected to the 1.5 V rail and the AVIN pin can be connected to a 2.2 V to 5.5 V rail.

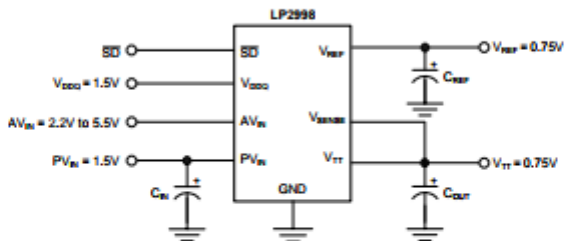


Figure 20. Recommended DDR-III Termination

If it is not desirable to use the 1.5 V - 2.5 V rail it is possible to connect the output stage to a 3.3 V rail. Care should be taken to not exceed the maximum junction temperature as the thermal dissipation increases with lower V_{TT} output voltages. For this reason it is not recommended to power PVIN off a rail higher than the nominal 3.3 V. The advantage of this configuration is that it has the ability to source and sink a higher maximum continuous current.

(6) Typical Application (continued)

(7) 9.2.2 DDR-II Applications

With the separate VDDQ pin and an internal resistor divider it is possible to use the LP2998 in applications utilizing DDR-II memory. Figure 21 and Figure 22 show several implementations of recommended circuits with output curves displayed in the *Typical Characteristics*. Figure 21 shows the recommended circuit configuration for DDR-II applications. The output stage is connected to the 1.8 V rail and the AVIN pin can be connected to either a 3.3 V or 5 V rail.

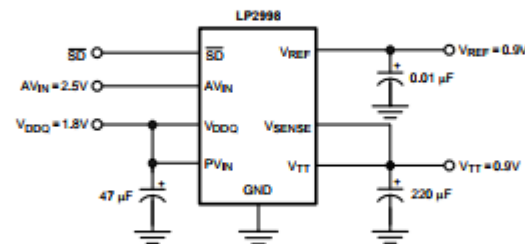


Figure 21. Recommended DDR-II Termination

If it is not desirable to use the 1.8 V rail it is possible to connect the output stage to a 3.3 V rail. Care should be taken to not exceed the maximum junction temperature as the thermal dissipation increases with lower V_{TT} output voltages. For this reason it is not recommended to power PVIN off a rail higher than the nominal 3.3 V. The advantage of this configuration is that it has the ability to source and sink a higher maximum continuous current.

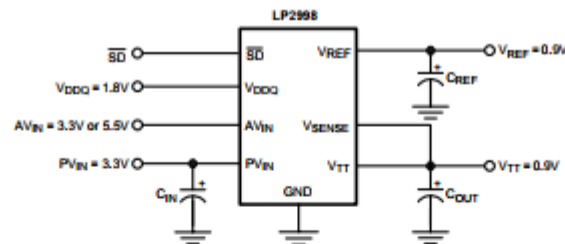


Figure 22. DDR-II Termination with Higher Voltage Rails

9.2.3 SSTL-2 Applications

For the majority of applications that implement the SSTL-2 termination scheme it is recommended to connect all the input rails to the 2.5 V rail. This provides an optimal trade-off between power dissipation and component count and selection. An example of this circuit can be seen in Figure 23.

Typical Application (continued)

This circuit permits termination in a minimum amount of board space and component count. Capacitor selection can be varied depending on the number of lines terminated and the maximum load transient. However, with motherboards and other applications where V_{TT} is distributed across a long plane it is advisable to use multiple bulk capacitors and addition to high frequency decoupling. Figure 29 shown below depicts an example circuit where 2 bulk output capacitors could be situated at both ends of the V_{TT} plane for optimal placement. Large aluminum electrolytic capacitors are used for their low ESR and low cost.

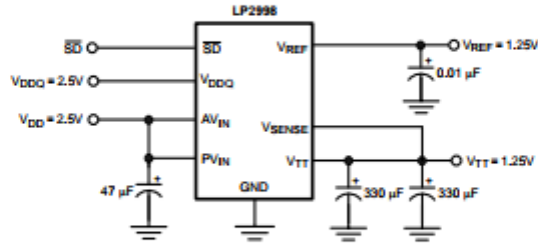


Figure 29. Typical SSTL-2 Application Circuit for Motherboards

In most PC applications an extensive amount of decoupling is required because of the long interconnects encountered with the DDR-SDRAM DIMMs mounted on modules. As a result bulk aluminum electrolytic capacitors in the range of 1000 μF are typically used.

9.2.5 HSTL Applications

The LP2998 can be easily adapted for HSTL applications by connecting V_{DDQ} to the 1.5 V rail. This will produce a V_{TT} and V_{REF} voltage of approximately 0.75 V for the termination resistors. AVIN and PVIN should be connected to a 2.5 V rail for optimal performance.

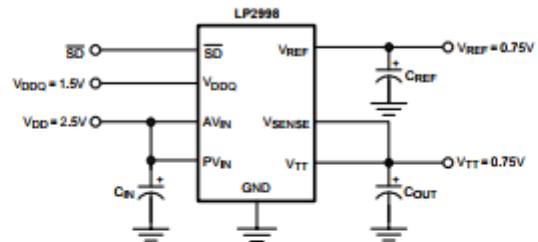


Figure 30. HSTL Application

9.2.6 QDR Applications

Quad data rate (QDR) applications utilize multiple channels for improved memory performance. However, this increase in bus lines has the effect of increasing the current levels required for termination. The recommended approach in terminating multiple channels is to use a dedicated LP2998 for each channel. This simplifies layout and reduces the internal power dissipation for each regulator. Separate V_{REF} signals can be used for each DIMM bank from the corresponding regulator with the chipset reference provided by a local resistor divider or one of the LP2998 signals. Because V_{REF} and V_{TT} are expected to track and the part to part variations are minor, there should be little difference between the reference signals of each LP2998.

10 Power Supply Recommendations

There are several recommendations for the LP2998 input power supply. An input capacitor is not required but is recommended for improved performance during large load transients to prevent the input rail from dropping. The input capacitor should be located as close as possible to the PVIN pin. Several recommendations exist dependent on the application required. A typical value recommended for AL electrolytic capacitors is 50 μF . Ceramic capacitors can also be used, a value in the range of 10 μF with X5R or better would be an ideal choice. The input capacitance can be reduced if the LP2998 is placed close to the bulk capacitance from the output of the 2.5 V DC-DC converter. If the two supply rails (AVIN and PVIN) are separated then the 47 μF capacitor should be placed as close as possible to the PVIN rail. An additional 0.1 μF ceramic capacitor can be placed on the AVIN rail to prevent excessive noise from coupling into the device.

11 Layout

11.1 Layout Guidelines

1. The input capacitor for the power rail should be placed as close as possible to the PVIN pin.
2. V_{SENSE} should be connected to the V_{TT} termination bus at the point where regulation is required. For motherboard applications an ideal location would be at the center of the termination bus.
3. V_{DDQ} can be connected remotely to the V_{DDQ} rail input at either the DIMM or the Chipset. This provides the most accurate point for creating the reference voltage.
4. For improved thermal performance excessive top side copper should be used to dissipate heat from the package. Numerous vias from the ground connection to the internal ground plane will help. Additionally these can be located underneath the package if manufacturing standards permit.
5. Care should be taken when routing the V_{SENSE} trace to avoid noise pickup from switching I/O signals. A 0.1 μF ceramic capacitor located close to the V_{SENSE} can also be used to filter any unwanted high frequency signal. This can be an issue especially if long V_{SENSE} traces are used.
6. V_{REF} should be bypassed with a 0.01 μF or 0.1 μF ceramic capacitor for improved performance. This capacitor should be located as close as possible to the V_{REF} pin.